

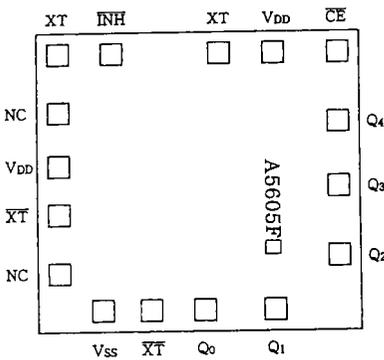
■ OVERVIEW

The SM5605F series are C-MOS LSIs for quartz oscillating module. Each LSI has a high frequency oscillating circuit and dividers with low current consumption. One of the output signals is a fundamental frequency and the others are divided frequencies. This series have two types of oscillating circuits. One is built-in capacitor for oscillating, and the other is the type of external capacitor.

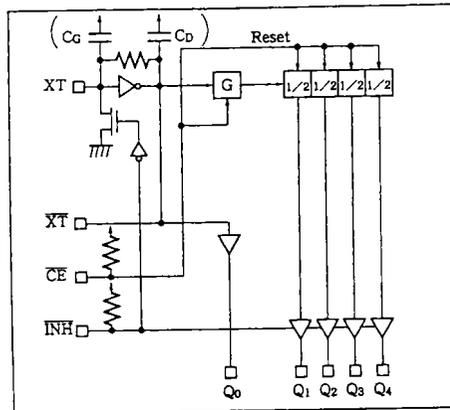
■ FEATURES

- Operating voltage (3 to 6V)
- Built-in feed back resistance of inverter amplifier
- Fundamental frequency and divided frequencies output
- Built-in capacitor for oscillating (FC type) CD-20pF (TYP), CG-20pF (TYP)
- Maximum frequency ... 30MHz
- Low current consumption
- Fan out 2TTL
- Standby function
- Chip form

■ PAD LOCATION



■ BLOCK DIAGRAM



■ PAD COORDINATES

UNIT: μm

NAME	X	Y
V _{SS}	285	155
XT	485	155
Q ₀	710	155
Q ₁	1060	155
Q ₂	1350	395
Q ₃	1350	675
Q ₄	1350	930
CE	1350	1245
V _{DD}	1045	1245
XT	845	1245
INH	465	1245
XT	155	1245
NC	155	955
V _{DD}	155	755
XT	155	555
NC	155	355

CHIP SIZE:

1.5mm × 1.4mm

CHIP THICKNESS:

400 ±30 μm

■ PAD DESCRIPTION

NAME	FUNCTION
XT	Input terminal for oscillating
XT	Output terminal for oscillating
INH	"L" Standby mode On chip pull-up resistance
CE	Output control for divided frequency Pull-up resistance
V _{DD}	Power-supply
V _{SS}	Ground
Q ₀	Output terminal for fundamental frequency
Q ₁₋₄	Output terminal for divided frequency

■ ABSOLUTE MAXIMUM RATING (V_{SS}=0V)

ITEM	SYMBOL	CONDITIONS	UNIT
Supply voltage	V _{DD}	V _{SS} -0.5 to V _{SS} +7.0	V
Input voltage	V _{IN}	V _{SS} -0.5 to V _{DD} +0.5	V
Output voltage	V _{OUT}	V _{SS} -0.5 to V _{DD} +0.5	V
Storage temperature	T _{STG}	-65 to +150	°C

■ RECOMMENDED OPERATIONAL CONDITIONS (V_{SS}=0V)

ITEM	SYMBOL	MIN	TYP	MAX	UNIT
Operating voltage	V _{DD}	3		6	V
Input voltage	V _{IN}	V _{SS}		V _{DD}	V
Operating temperature	T _{OPR}	-40		+85	°C

■ ELECTRICAL CHARACTERISTICS

V_{DD}=5V, Ta=-40°C ~ +85°C

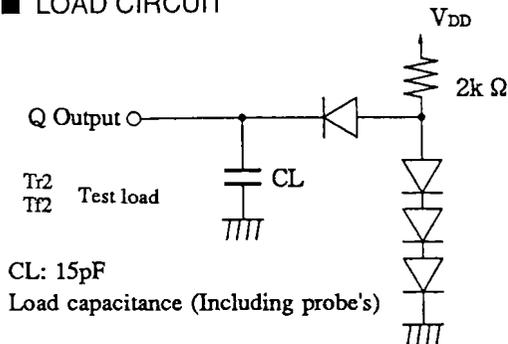
ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT	
Output current 1 ("H" level)	I _{OH1}	Exclude \overline{XT} terminal	V _{DH} = 0.9V _{DD}	1.0		mA	
Output current 1 ("L" level)	I _{OL1}	Fig. 1, V _{DD} = -5V ±0.5V	V _{OL} =0.1V _{DD}	3.2			
Output current 2 ("H" level)	I _{OH2}	Exclude XT terminal	V _{OH} =2.4V	1.0		mA	
Output current 2 ("L" level)	I _{OL2}	Fig. 1, V _{DD} =5V ±0.5V	V _{OL} =0.4V	3.2			
Output current 3 ("H" level)	I _{OH3}	V _{OH} =4.5V	Ta=25°C, V _{DD} = 5V	3.5	5	6.5	mA
Output current 3 ("L" level)	I _{OL3}	V _{OL} =0.5V	XT terminal, Fig. 6	3.5	5	6.5	
Input voltage ("H" level)	V _{IH}	INH, CE terminal		0.8V _{DD}		V	
Input voltage ("L" level)	V _{IL}	V _{DD} =-5V ±0.5V			0.2V _{DD}		
Input bias voltage	V _{XBS}	XT terminal Ta=25°C	Fig. 2	2.2	2.5	2.8	V
Current consumption 1	I _{DD1}	CE, INH=OPEN	Fig. 3		4.5	6.5	
Current consumption 2	I _{DD2}	CE="L", INH=OPEN	Fig. 3		3.5	5.5	
Current consumption 3	I _{DD3}	INH="L", CE=OPEN			0.1	0.4	mA
Pull-up resistance	R _{UP}	Ta=25°C	Fig. 4	20	40	80	
Feed back resistance	R _F	Ta=25°C	Fig. 5	1		5	
Internal capacitor	CG	f=1MHz		10	20	35	pF
	CD	f=1MHz		10	20	35	

■ SWITCHING CHARACTERISTICS f=16MHz (Except \overline{XT} terminal), V_{DD}=-5V ±0.5V, Ta=25°C

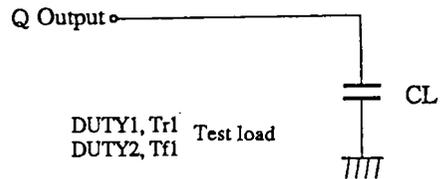
ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT	
Output rise time 1	T _{r1}	Fig. 3, Circuit-2, 0.1V _{DD} → 0.9V _{DD}		5	10	nS	
Output rise time 2	T _{r2}	Fig. 3, Circuit-1, 0.4V _{DD} → 2.4V _{DD}		5	10		
Output fall time 1	T _{f1}	Fig. 3, Circuit-2, 0.9V _{DD} → 0.1V _{DD}		5	10	nS	
Output fall time 2	T _{f2}	Fig. 3, Circuit-1, 2.4V _{DD} → 0.4V _{DD}		5	10		
Duty of fundamental output	DUTY1	Fig-3, Circuit-2, V _{DD} = 5V	Q0	40		60	%
Duty of divided output	DUTY2		Q1 to Q4	45		55	
Output delay time 1	T _{PLH1}	Q1 output monitor			30	nS	
Output delay time 1	T _{PHL1}	V _{DD} =5V at INH			35		70
Output delay time 2	T _{PLH2}	Q1 output monitor			70	140	
Output delay time 2	T _{PHL2}	V _{DD} =5V at CE			70		140

f_o: Input frequency to XT terminal

■ LOAD CIRCUIT



Circuit-1



Circuit-2

CL: 15pF
Load capacitance (Including probe's)

CL: 15pF
Load capacitance (Including probe's)

■ TEST CIRCUIT

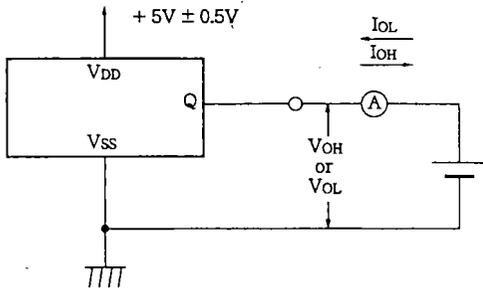


Fig. 1

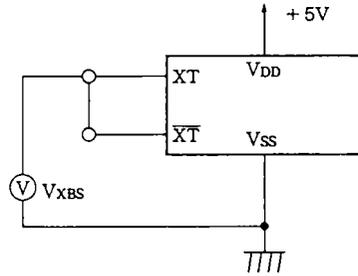
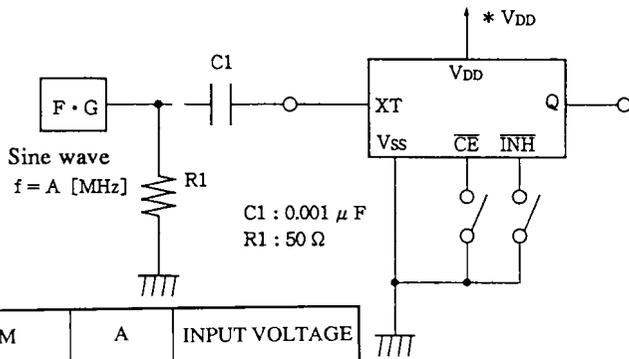


Fig. 2

* Test of I_{DD}

$V_{DD}=5V$

* Test of switching characteristics $V_{DD}=5V \pm 0.5V$



ITEM	A	INPUT VOLTAGE
I_{DD}	16MHz	$4V_{pp}$
Switching item	16MHz	$5V_{pp}$

Fig. 3

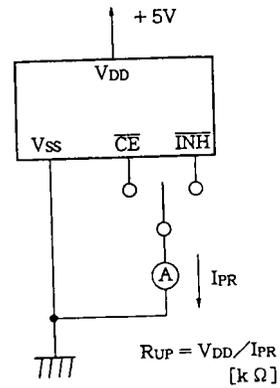


Fig. 4

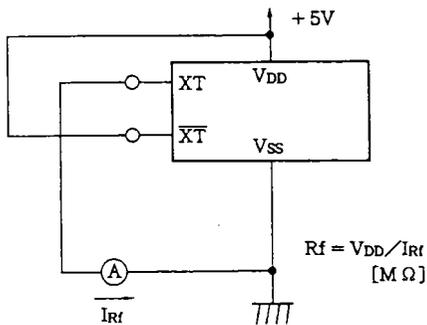


Fig. 5

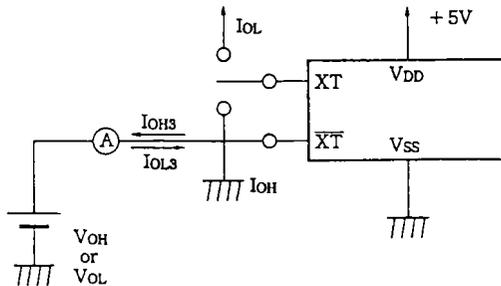
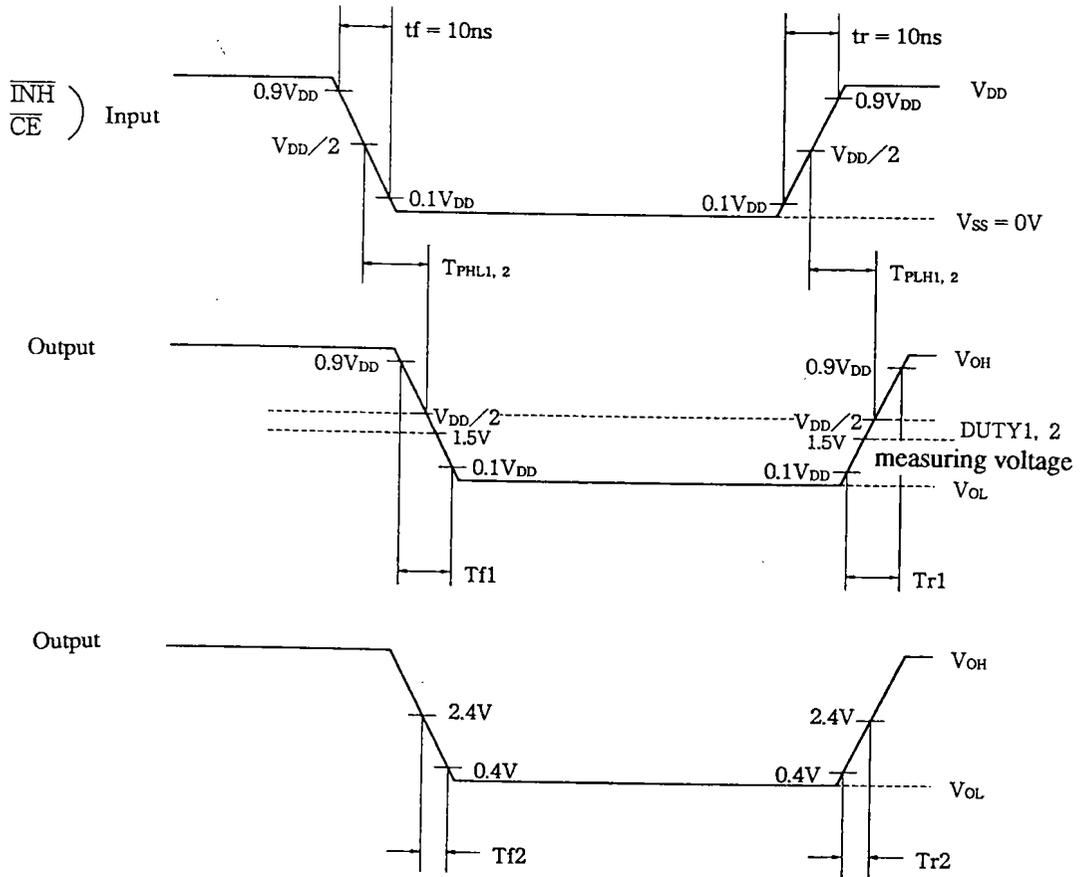


Fig. 6

■ WAVEFORMS FOR SWITCHING TIME



■ SERIES TABLE

SERIES	Built-in capacity type
SM5605FA	No capacity
SM5605FC	CD, CG=20pF (TYP.)

■ FUNCTIONAL TABLE

$\overline{\text{INH}}$	$\overline{\text{CE}}$	Q ₀	Q ₁	Q ₂	Q ₃	Q ₄
H or OPEN	H or OPEN	f _o	f _o /2	f _o /4	f _o /8	f _o /16
H or OPEN	L	f _o	L	←	←	←
L	H or OPEN	L	←	←	←	←
L	L	L	←	←	←	←